

BSS138PS

60 V, 320 mA dual N-channel Trench MOSFET Rev. 1 — 2 November 2010

Product data sheet

Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{DS}	drain-source voltage	$T_{amb} = 25 ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	T_{amb} = 25 °C; V_{GS} = 10 V	[1] -	-	320	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 300 \text{mA}$	<u>[2]</u> -	0.9	1.6	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



^[2] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.01.$

60 V, 320 mA dual N-channel Trench MOSFET

2. Pinning information

Table 2. Pinning

Table 2.	ı ııııııı			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	D- D- D.	
2	G1	gate1	6 5 4	D ₁ D ₂
3	D2	drain2		
4	S2	source2	0	
5	G2	gate2	<u> </u> 1	
6	D1	drain1		S_1 G_1 S_2 G_2
				msd901

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BSS138PS	SC-88	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BSS138PS	NZ*

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V_{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I_D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	320	mA
		T _{amb} = 100 °C	-	200	mA
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C;$ single pulse; $t_p \le 10 \mu s$	-	1.2	Α

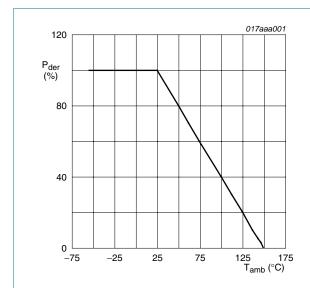
60 V, 320 mA dual N-channel Trench MOSFET

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

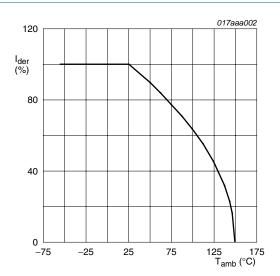
Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	P _{tot} total power dissipation	$T_{amb} = 25 ^{\circ}C$	[2] -	280	mW
			[1] -	320	mW
		$T_{sp} = 25 ^{\circ}C$	-	960	mW
Source-d	rain diode				
Is	source current	$T_{amb} = 25 ^{\circ}C$	<u>[1]</u> -	290	mA
Per device	e				
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] -	420	mW
T _j	junction temperature			150	°C
T _{amb}	ambient temperature		–55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

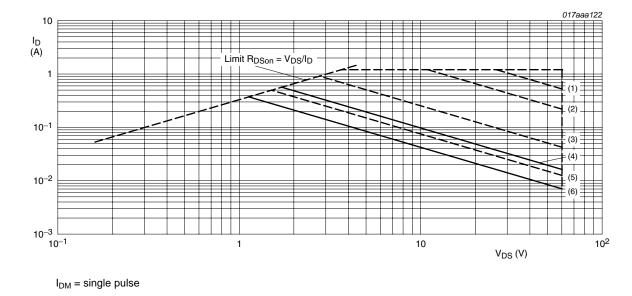
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

60 V, 320 mA dual N-channel Trench MOSFET



- (1) $t_p = 100 \, \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \,^{\circ}C$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Per transistor: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	<u>[1]</u> -	390	445	K/W
	junction to ambient		[2] _	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W
Per device	•					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

60 V, 320 mA dual N-channel Trench MOSFET

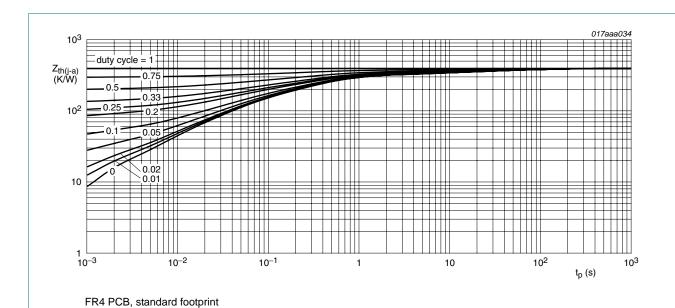
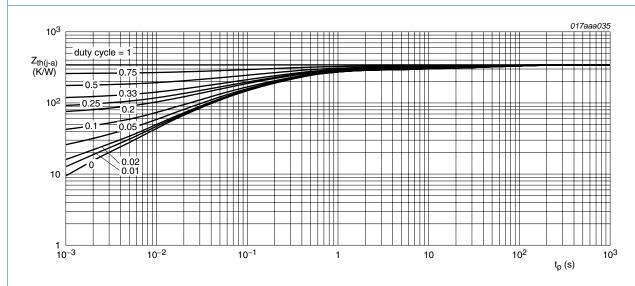


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 320 mA dual N-channel Trench MOSFET

7. Characteristics

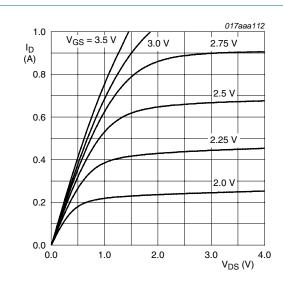
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	0.9	1.2	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance		[1]			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 300 \text{ mA}$	-	0.9	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	[1] -	700	-	mS
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 300 \text{ mA};$	-	0.72	8.0	nC
Q _{GS}	gate-source charge	$V_{DS} = 30 \text{ V};$	-	0.14	-	nC
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}$	-	0.24	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	38	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V};$	-	2	6	ns
t _r	rise time	$R_L = 250 \Omega;$	-	3	-	ns
t _{d(off)}	turn-off delay time	$V_{GS} = 10 \text{ V};$ $R_G = 6 \Omega$	-	9	20	ns
t _f	fall time	_ •	-	4	-	ns
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

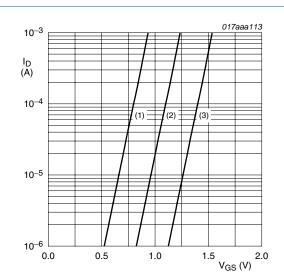
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

60 V, 320 mA dual N-channel Trench MOSFET



 $T_{amb} = 25 \, ^{\circ}C$

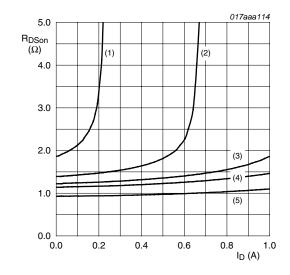
Fig 6. Per transistor: Output characteristics: drain current as a function of drain-source voltage; typical values



 T_{amb} = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

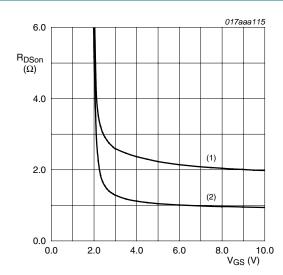
Fig 7. Per transistor: Sub-threshold drain current as a function of gate-source voltage



T_{amb} = 25 °C

- (1) $V_{GS} = 2 V$
- (2) $V_{GS} = 2.5 \text{ V}$
- (3) $V_{GS} = 3 V$
- (4) $V_{GS} = 3.5 \text{ V}$
- (5) $V_{GS} = 10 \text{ V}$

Fig 8. Per transistor: Drain-source on-state resistance as a function of drain current; typical values

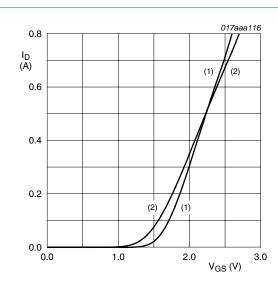


 $I_D = 300 \text{ mA}$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Per transistor: Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

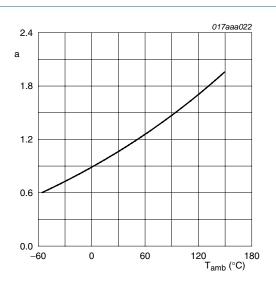


$$V_{DS} > I_D \times R_{DSon}$$

(1)
$$T_{amb} = 25 \,^{\circ}C$$

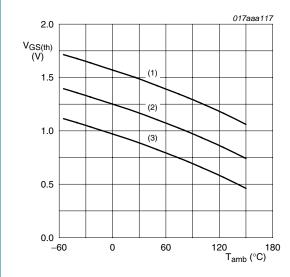
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Per transistor: Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

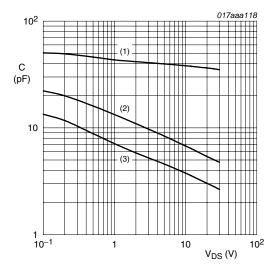
Fig 11. Per transistor: Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Per transistor: Gate-source threshold voltage as a function of ambient temperature

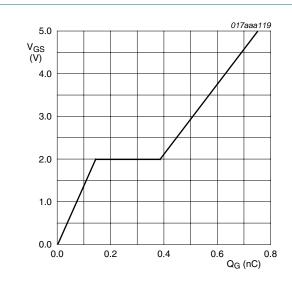


f = 1 MHz; V_{GS} = 0 V

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Per transistor: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET



 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Per transistor: Gate-source voltage as a function of gate charge; typical values

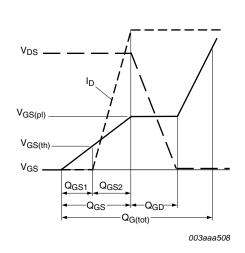
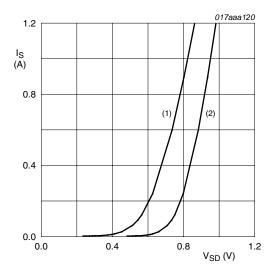


Fig 15. Per transistor: Gate charge waveform definitions



 $V_{GS} = 0 V$

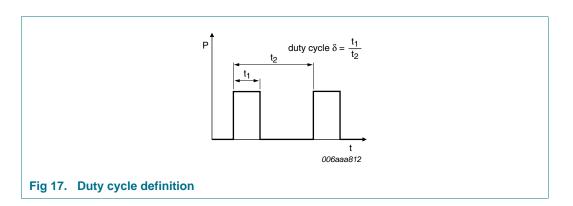
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Per transistor: Source current as a function of source-drain voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 320 mA dual N-channel Trench MOSFET

9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

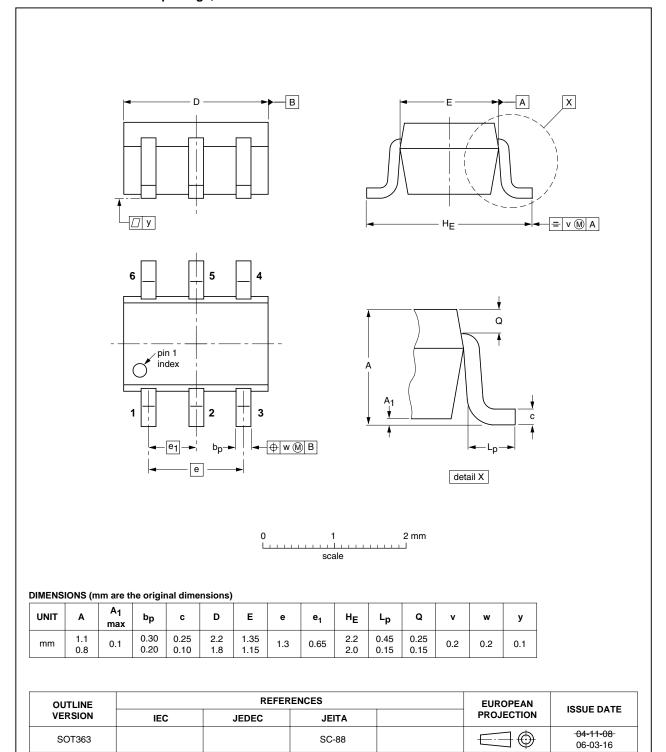
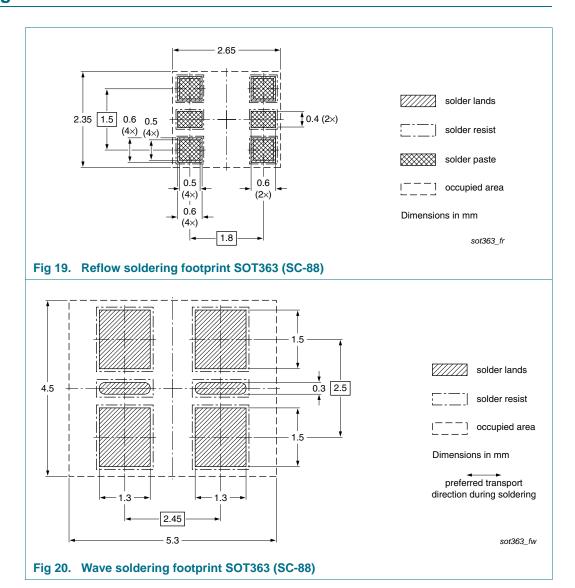


Fig 18. Package outline SOT363 (SC-88)

All information provided in this document is subject to legal disclaimers.

60 V, 320 mA dual N-channel Trench MOSFET

10. Soldering



60 V, 320 mA dual N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138PS v.1	20101102	Product data sheet	-	-

60 V, 320 mA dual N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or

malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

BSS138PS

All information provided in this document is subject to legal disclaimers.

60 V, 320 mA dual N-channel Trench MOSFET

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

60 V, 320 mA dual N-channel Trench MOSFET

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics
7	Characteristics
8	Test information
8.1	Quality information
9	Package outline
10	Soldering 12
11	Revision history
12	Legal information14
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Trademarks15
13	Contact information
14	Contents